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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/774.427	01/30/2001	Shunnei Yamazaki	07977/115003/US3251D1D1	3966

20985 7590 04/14/2003 FISH & RICHARDSON, PC 4350 LA JOLLA VILLAGE DRIVE SUITE 500 SAN DIEGO, CA 92122

EXA	MINER			
COLEMAN, WILLIAM D				
ART UNIT	PAPER NUMBER			

2823 DATE MAILED: 04/14/2003

Please find below and/or attached an Office communication concerning this application or proceeding.





# Office Action Summary

Application No.	Applicant(s)	
09/774,427	YAMAZAKI ET AL.	
Examiner	Art Unit	

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --Period for Reply

W. David Coleman

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM

THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailling date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If the Openiod reply is specified above, the maximum statutory period will apply and will expire SIX (6) MOITHS from the maling idea of this communication.

  Failure to reply within the set or extended prior for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).

  Any reply received by the Office later than three months after the maling date of this communication, even if timely field, may reduce on any

Status	ed patent term adjustment. See 37 CFR 1.704(b).					
1)⊠	Responsive to communication(s) filed on <u>06 February 2003</u> .					
2a)	This action is <b>FINAL</b> . 2b)⊠ This action is	non-final.				
3)[	3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> . 1935 C.D. 11, 453 O.G. 213.					
Disposit	Disposition of Claims					
4)⊠	☑ Claim(s) 1-11 is/are pending in the application.					
	4a) Of the above claim(s) is/are withdrawn from consideration.					
5)	Claim(s) is/are allowed.					
6)⊠	Claim(s) <u>1-11</u> is/are rejected.					
7)	Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and/or election requirement.  Application Papers						
9) The specification is objected to by the Examiner.						
	The drawing(s) filed on is/are: a) accepted or b)	chiected to by the Evaminer				
10)[	Applicant may not request that any objection to the drawing(s)					
11)	The proposed drawing correction filed on is: a) are	**				
,	If approved, corrected drawings are required in reply to this Off					
12)	The oath or declaration is objected to by the Examiner.					
,	under 35 U.S.C. §§ 119 and 120					
13)⊠	Acknowledgment is made of a claim for foreign priority un-	der 35 U.S.C. § 119(a)-(d) or (f).				
a)	☑ All b)☐ Some * c)☐ None of:					
	1. Certified copies of the priority documents have been	n received.				
	2. Certified copies of the priority documents have been received in Application No. 09/206,637.					
3. Copies of the certified copies of the priority documents have been received in this National Stage						
application from the International Bureau (PCT Rule 17.2(a)).  * See the attached detailed Office action for a list of the certified copies not received.						
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).						
a) The translation of the foreign language provisional application has been received.						
15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.						
Attachmen		_				
1) ☐ Notice of References Cited (PTO-982)         4) ☐ Interview Summary (PTO-413) Paper No(s)						

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#### DETAILED ACTION

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on February 6, 2003 has been entered.

### Claim Rejections - 35 USC § 102

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

- The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) do not apply to the examination of this application as the application being examined was not (1) filed on or after November 29, 2000, or (2) voluntarily published under 35 U.S.C. 122(b). Therefore, this application is examined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).
- Claims 8, 9 and 10 are rejected under 35 U.S.C. 102(e) as being anticipated by Wakai et al., U.S. Patent 5,821,137.
- 3. Pertaining to claims 8 and 9, <u>Wakai</u> discloses a semiconductor device as claimed. See FIG. 4E, where <u>Wakai</u> teaches a semiconductor device having at least one thin film transistor formed over a substrate, said thin film transistor comprising:

a semiconductor layer 66 having source and drain region (not numbered) and a channel forming region therebetween; and

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a gate electrode 62 adjacent to said channel forming region with a gate insulating layer 64 interposed therebetween,

wherein said channel forming region directly contacts with source and drain regions, and also in contact with the channel region,

wherein a pair of portions containing n-type and p-type impurities are formed adjacent to said source and drain regions respectively,

wherein said pair of portions have the same conductivity type as said source and drain regions, and

wherein an electrode 79 is connected to at least one of said pair of portions.

Pertaining to claim 10, <u>Wakai</u> discloses wherein said channel forming region contains an
impurity imparting one conductivity (please note that the LDD is around the channel forming
region).

## Claim Rejections - 35 USC § 103

- 5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. Claim11 is rejected under 35 U.S.C. 103(a) as being unpatentable over Wakai et al., U.S. Patent 5,821,137 as applied to claims 8, 9 and 10 above, and further in view of Katayama et al., U.S. Patent 4,613,382.
- Wakai discloses a semiconductor device substantially as claimed as discussed above.
   However, Wakai fails to disclose wherein the semiconductor film contains an impurity

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containing hydrogen and halogen. Katayama teaches wherein the semiconductor film contains hydrogen and halogen. See column 1, lines 11-57 of Katayama, where a polysilicon film contains both hydrogen and a halogen (i.e., fluorine, chlorine, bromine, and iodine). In view of Katayama, it would have been obvious to one of ordinary skill in the art to incorporate a hydrogen and halogen into the semiconductor device of Wakai because it has a reduced influence of the grain boundaries (column 1, lines 36-38).

### **Double Patenting**

- 8. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See In re Goodman, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); In re Longi, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); In re Van Ornum, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); In re Vogel, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, In re Thorington, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).
- 9. A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).
- Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).
- 11. Claims 1-7 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claim 1 of U.S. Patent No. 6,194,762. Although the conflicting claims are not identical, they are not patentably distinct from each other because claim 1 of U.S. Patent 6,192,762 does not explicitly teach a gate electrode adjacent to the channel forming region with a gate insulating layer interposed therebetween having an electrode connected to at least one of said pair of portions. However, these are well known and necessary features or components of MOS thin film transistors.

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12. Claims 8-11 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claim 1 of U.S. Patent No. 6,194,762. Although the conflicting claims are not identical, they are not patentably distinct from each other because claims 1-5 of U.S. Patent 6,194,762 do not explicitly teach an active matrix circuit and a driver circuit having a first and second thin film transistors. However, the use of first and second thin film transistors in the driver circuit and the active matrix circuit are well known.

#### Conclusion

13. Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is 703-305-0004. The examiner can normally be reached on 9:00 AM-5:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7721 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

W. David Coleman Examiner Art Unit 2823

WDC April 4, 2003